Distributed by:



The content and copyrights of the attached material are the property of its owner.

Jameco Part Number 39651TI

TMS27C010A 131 072 BY 8-BIT UV ERASABLE TMS27PC010A 131 072 BY 8-BIT PROGRAMMABLE READ-ONLY MEMORIES SMLS110C – NOVEMBER 1990 – REVISED SEPTEMBER 1997

- Organization . . . 131072 by 8 Bits
- Single 5-V Power Supply
- Operationally Compatible With Existing Megabit EPROMs
- Industry Standard 32-Pin Dual-In-line Package and 32-Lead Plastic Leaded Chip Carrier
- All Inputs/Outputs Fully TTL Compatible
- Maximum Access/Minimum Cycle Time V_{CC} ± 10% '27C/PC010A-10 100 ns
 - ²27C/PC010A-12 120 ns ²27C/PC010A-15 150 ns ²27C/PC010A-20 200 ns
- 8-Bit Output For Use in Microprocessor-Based Systems
- Very High-Speed SNAP! Pulse Programming
- Power-Saving CMOS Technology
- 3-State Output Buffers
- 400-mV Minimum DC Noise Immunity With Standard TTL Loads
- Latchup Immunity of 250 mA on All Input and Output Pins
- No Pullup Resistors Required
- Low Power Dissipation (V_{CC} = 5.5 V)
 - Active ... 165 mW Worst Case
 Standby ... 0.55 mW Worst Case
 - (CMOS-Input Levels)
- Temperature Range Options

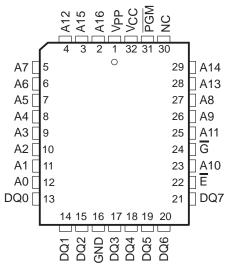
description

The TMS27C010A series are 131072 by 8-bit (1048576-bit), ultraviolet (UV) light erasable, electrically programmable read-only memories (EPROMs).

The TMS27PC010A series are 131072 by 8-bit (1048576-bit), one-time programmable (OTP) electrically programmable read-only memories (PROMs).

	-		KAG VIEW	_	
V _{PP} A16 A15 A12 A7 A6 A5 A4 A3 A2 A1 A0 DQ0 DQ1		TOP 1 2 3 4 5 6 7 8 9 10 11 12 13 14	VIEW 32 31 30 29 28 27 26 25 24 23 22 21 20 19		V _{CC} PGM NC A14 A13 A8 A9 A11 G A10 E DQ7 DQ6 DQ5
DQ2 GND		15 16	18 17		DQ4 DQ3
	FN		~ K A G	F	





I	PIN NOMENCLATURE
A0-A16 DQ0-DQ7 E G GND NC PGM VCC	Address Inputs Inputs (programming)/Outputs Chip Enable Output Enable Ground No Internal Connection Program 5-V Power Supply
VPP	13-V Power Supply†

[†]Only in program mode



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



Copyright © 1997, Texas Instruments Incorporated

SMLS110C - NOVEMBER 1990 - REVISED SEPTEMBER 1997

description (continued)

These devices are fabricated using power-saving CMOS technology for high speed and simple interface with MOS and bipolar circuits. All inputs (including program data inputs) can be driven by Series 74 TTL circuits without the use of external pullup resistors. Each output can drive one Series 74 TTL circuit without external resistors.

The TMS27C010A EPROM is offered in a dual-in-line ceramic package (J suffix) designed for insertion in mounting hole rows on 15,2-mm (600-mil) centers. The TMS27C010A is also offered with two choices of temperature ranges, 0°C to 70°C (JL suffix) and -40°C to 85°C (JE suffix). See Table 1.

The TMS27PC010A OTP PROM is offered in a 32-pin, plastic leaded chip carrier package using 1,25-mm (50-mil) lead spacing (FM suffix). The TMS27PC010A is offered with two choices of temperature ranges, 0°C to 70°C (FML suffix) and -40°C to 85°C (FME suffix). See Table 1.

EPROM AND OTP PROM	SUFFIX FOR OPERATING FREE- AIR TEMPERATURE RANGES						
	0°C to 70°C	-40° C to 85° C					
TMS27C010A-xxx	JL	JE					
TMS27PC010A-xxx	FML	FME					

Table 1. Temperature Range Suffixes

These EPROMs and OTP PROMs operate from a single 5-V supply (in the read mode), thus are ideal for use in microprocessor-based systems. One other 13-V supply is needed for programming. All programming signals are TTL level. These devices are programmable using the SNAP! Pulse programming algorithm. The SNAP! Pulse programming algorithm uses a V_{PP} of 13 V and a V_{CC} of 6.5 V for a nominal programming time of thirteen seconds. For programming outside the system, existing EPROM programmers can be used. Locations can be programmed singly, in blocks, or at random.

operation

The seven modes of operation are listed in Table 2. The read mode requires a single 5-V supply. All inputs are TTL level except for V_{PP} during programming (13 V for SNAP! Pulse), and 12 V on A9 for signature mode.

				MODE				
FUNCTION	READ	OUTPUT DISABLE	STANDBY	PROGRAMMING	VERIFY	PROGRAM INHIBIT	SIGNATU	RE MODE
Ē	VIL	VIL	VIH	VIL	VIL	VIH	V	IL
G	VIL	VIH	Х	VIH	VIL	Х	V	IL
PGM	Х	Х	Х	VIL	VIH	Х	>	<
VPP	VCC	VCC	VCC	VPP	VPP	VPP	Vc	C
VCC	VCC	VCC	VCC	Vcc	VCC	VCC	Vc	CC
A9	Х	Х	Х	Х	Х	Х	∨ _H ‡	∨ _H ‡
A0	Х	Х	Х	Х	Х	Х	VIL	VIH
							CODE	
DQ0-DQ7	Data Out	Hi-Z	Hi-Z	Data In	Data Out	Hi-Z	MFG	DEVICE
<u> </u>							97	D6

Table 2. Operation Modes

† X can be VIL or VIH.

 $^{\ddagger}V_{H} = 12 V \pm 0.5 V.$



read/output disable

When the outputs of two or more TMS27C010As or TMS27PC010As are connected in parallel on the same bus, the output of any particular device in the circuit can be read with no interference from competing outputs of the other devices. To read the output of a single device, a low-level signal is applied to the \overline{E} and \overline{G} pins. All other devices in the circuit should have their outputs disabled by applying a high level signal to one of these pins.

latchup immunity

Latchup immunity on the TMS27C010A and TMS27PC010A is a minimum of 250 mA on all inputs and outputs. This feature provides latchup immunity beyond any potential transients at the P.C. board level when the devices are interfaced to industry standard TTL or MOS logic devices. The input/output layout approach controls latchup without compromising performance or packing density.

power down

Active I_{CC} supply current can be reduced from 30 mA to 500 μ A by applying a high TTL input on \overline{E} and to 100 μ A by applying a high CMOS input on \overline{E} . In this mode all outputs are in the high-impedance state.

erasure (TMS27C010A)

Before programmig, the TMS27C010A EPROM is erased by exposing the chip through the transparent lid to a high intensity UV light (wavelength 2537 Å). The recommended minimum exposure dose (UV intensity × exposure time) is 15-W·s/cm². A typical 12-mW/cm², filterless UV lamp erases the device in 21 minutes. The lamp should be located about 2.5 cm above the chip during erasure. After erasure, all bits are in the high state. Normal ambient light contains the correct wavelength for erasure, therefore, when using the TMS27C010A, the window must be covered with an opaque label. After erasure (all bits in logic high state), logic lows are programmed into the desired locations. A programmed low can be erased only by UV light.

initializing (TMS27PC010A)

The one-time programmable TMS27PC010A PROM is provided with all bits in the logic high state, then logic lows are programmed into the desired locations. Logic lows programmed into an OTP PROM cannot be erased.

SNAP! Pulse programming

The TMS27C010A and TMS27PC010A are programmed using the TI SNAP! Pulse programming algorithm illustrated by the flowchart in Figure 1, which programs in a nominal time of thirteen seconds. Actual programming time varies as a function of the programmer used.

The SNAP! Pulse programming algorithm uses an initial pulse of 100 microseconds (μ s) followed by a byte verification to determine when the addressed byte has been successfully programmed. Up to 10 (ten) 100- μ s pulses per byte are provided before a failure is recognized.

The programming mode is achieved when $V_{PP} = 13 \text{ V}$, $V_{CC} = 6.5 \text{ V}$, $\overline{E} = V_{IL}$, $\overline{G} = V_{IH}$. Data is presented in parallel (eight bits) on pins DQ0 through DQ7. Once addresses and data are stable, \overline{PGM} is pulsed low.

More than one device can be programmed when the devices are connected in parallel. Locations can be programmed in any order. When the SNAP! Pulse programming routine is complete, all bits are verified with $V_{CC} = V_{PP} = 5 \text{ V} \pm 10\%$.

program inhibit

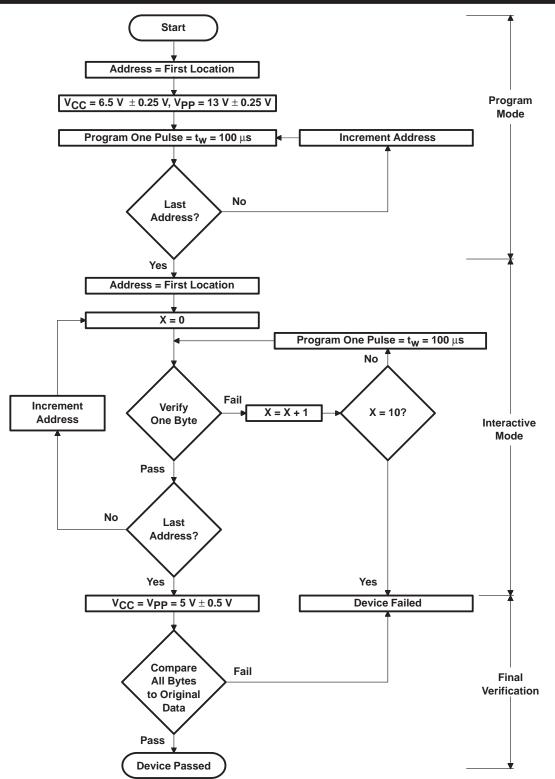
Programming can be inhibited by maintaining a high level input on the \overline{E} or \overline{PGM} pins.

program verify

Programmed bits can be verified with $V_{PP} = 13 \text{ V}$ when $\overline{G} = V_{IL}$, $\overline{E} = V_{IL}$, and $\overline{PGM} = V_{IH}$.



SMLS110C - NOVEMBER 1990 - REVISED SEPTEMBER 1997







signature mode

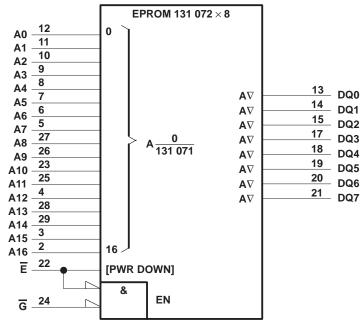
The signature mode provides access to a binary code identifying the manufacturer and type. This mode is activated when A9 (pin 26) is forced to 12 V. Two identifier bytes are accessed by toggling A0. All other addresses must be held low. The signature code for these devices is 97D6. A0 low selects the manufacturer's code 97 (Hex), and A0 high selects the device code D6 (Hex), as shown in Table 3.

	_	-	_	PI	NS	_	_	-	-
A0	DQ7	DQ6	DQ5	DQ4	DQ3	DQ2	DQ1	DQ0	HEX
VIL	1	0	0	1	0	1	1	1	97
VIH	1	1	0	1	0	1	1	0	D6
	VIL	V _{IL} 1	V _{IL} 1 0	V _{IL} 1 0 0	A0 DQ7 DQ6 DQ5 DQ4 VIL 1 0 0 1	V _{IL} 1 0 0 1 0	A0 DQ7 DQ6 DQ5 DQ4 DQ3 DQ2 V _{IL} 1 0 0 1 0 1	A0 DQ7 DQ6 DQ5 DQ4 DQ3 DQ2 DQ1 VIL 1 0 0 1 0 1 1	A0 DQ7 DQ6 DQ5 DQ4 DQ3 DQ2 DQ1 DQ0 V _{IL} 1 0 0 1 0 1 1 1

Table 3. Signature Mode

 $^{\dagger}\overline{E} = \overline{G} = V_{IL}$, A1–A8 = V_{IL}, A9 = V_H, A10–A16 = V_{IL}, V_{PP} = V_{CC}.

logic symbol[‡]



[‡]This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. J package illustrated.



SMLS110C - NOVEMBER 1990 - REVISED SEPTEMBER 1997

absolute maximum ratings over operating free-air temperature range (unless otherwise noted) [†]
Supply voltage range, V _{CC} (see Note 1)
Supply voltage range, VPP –0.6 V to 14 V
Input voltage range, All inputs except A9 Input voltage range, All inputs except A9
A9 –0.6 V to 13.5 V
Output voltage range, with respect to V _{SS} (see Note 1)
Operating free-air temperature range ('27C010AJL,
'27PC010AFML)
Operating free-air temperature range ('27C010AJE,
27PC010AFME)
Storage temperature range, T _{stg} 65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
NOTE 1: All voltage values are with respect to GND.

recommended operating conditions

				27C0 27C0	13 13.25 V _{CC} +0.5 2 V _{CC} +0.5 0.8 GND+0.2 70		UNIT
				MIN	NOM	MAX	
Vee	Supply	Read mode (see Note 2)		4.5	5	5.5	V
Vcc	voltage	SNAP! Pulse programming	algorithm	6.25	6.5	6.75	V
	Supply	Read mode (see Note 3)		VCC-0.6	Vcc	VCC+0.6	V
VPP	voltage	SNAP! Pulse programming	algorithm	12.75	13	13.25	V
	Lligh lovel o		TTL	2		V _{CC} +0.5	V
VIH	High-level d	lc input voltage	CMOS	V _{CC} -0.2		V _{CC} +0.5	V
Ma			TTL	- 0.5		0.8	V
VIL	Low-level d	c input voltage	CMOS	- 0.5		GND+0.2	v
т _А	Operating fr	ree-air temperature	'27C010AJL '27PC010AFML	0		70	°C
ТА	Operating fr	ree-air temperature	'27C010AJE '27PC010AFME	- 40		85	°C

NOTES: 2. V_{CC} must be applied before or at the same time as V_{PP} and removed after or at the same time as V_{PP}. The device must not be inserted into or removed from the board when V_{PP} or V_{CC} is applied.

3. During programming, Vpp must be maintained at 13 V \pm 0.25 V.



TMS27C010A 131 072 BY 8-BIT UV ERASABLE TMS27PC010A 131 072 BY 8-BIT PROGRAMMABLE READ-ONLY MEMORIES SMLS110C - NOVEMBER 1990 - REVISED SEPTEMBER 1997

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature

	PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
Vall	High lovel de output voltage		I _{OH} = - 20 μA	V _{CC} -0.2		V
∨он	High-level dc output voltage		I _{OH} = -2.5 mA	3.5		v
Val			I _{OL} = 2.1 mA		0.4	V
VOL	Low-level dc output voltage		I _{OL} = 20 μA		0.1	v
Ιį	Input current (leakage)		$V_{I} = 0 V \text{ to } 5.5 V$		±1	μΑ
10	Output current (leakage)		$V_{O} = 0 V \text{ to } V_{CC}$		±1	μA
IPP1	Vpp supply current		Vpp = V _{CC} = 5.5 V		10	μΑ
IPP2	VPP supply current (during program pu	lse)	Vpp = 13 V		50	mA
		TTL-input level	$V_{CC} = 5.5 \text{ V}, \overline{E} = V_{IH}$	500		
ICC1	V _{CC} supply current (standby)	CMOS-input level	$V_{CC} = 5.5 \text{ V}, \overline{E} = V_{CC} \pm 0.2 \text{ V}$		100	μA
I _{CC2}	V _{CC} supply current (active) (output ope	en)	$V_{CC} = 5.5 V$, $E = V_{IL}$ $t_{cycle} = minimum cycle time†,outputs open$		30	mA

[†] Minimum cycle time = maximum access time.

capacitance over recommended ranges of supply voltage and operating free-air temperature, f = 1 MHz $\!$

	PARAMETER	TEST CONDITIONS	MIN	TYP§	MAX	UNIT
Cl	Input capacitance	$V_{I} = 0 V$, $f = 1 MHz$		4	8	рF
CO	Output capacitance	$V_{O} = 0 V, f = 1 MHz$		6	10	рF

[‡] Capacitance measurements are made on sample basis only.

§ All typical values are at $T_A = 25^{\circ}C$ and nominal voltages.

switching characteristics over recommended ranges of operating conditions (see Notes 4 and 5)

	PARAMETER	TEST CONDITIONS	27C01		'27C010 '27PC01		'27C010 '27PC01		'27C010 '27PC01		UNIT
		CONDITIONS	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
ta(A)	Access time from address			100		120		150		200	ns
ta(E)	Access time from chip enable	<u>.</u>		100		120		150		200	ns
ten(G)	Output enable time from \overline{G}	CL = 100 pF, 1 Series 74		55		55		75		75	ns
t _{dis}	Output disable time from \overline{G} or \overline{E} , whichever occurs first [¶]	TTL load, Input $t_r \le 20$ ns,	0	50	0	50	0	60	0	60	ns
t _{V(A)}	Output data valid time after change of address, \overline{E} , or \overline{G} , whichever occurs first¶	Input t _f ≤ 20 ns	0		0		0		0		ns

¶ Value calculated from 0.5-V delta to measured output level.

NOTES: 4. For all switching characteristics the input pulse levels are 0.4 V to 2.4 V. Timing measurements are made at 2 V for logic high and 0.8 V for logic low (see Figure 2).

5. Common test conditions apply for t_{dis} except during programming.



switching characteristics for programming: V_{CC} = 6.5 V and V_{PP} = 13 V (SNAP! Pulse), T_A = 25°C (see Note 4)

	PARAMETER Disable time, output disable time from G Enable time, output enable time from G		MAX	UNIT
^t dis(G)		0	130	ns
ten(G)	Enable time, output enable time from \overline{G}		150	ns

NOTE 4: For all switching characteristics the input pulse levels are 0.4 V to 2.4 V. Timing measurements are made at 2 V for logic high and 0.8 V for logic low (see the ac testing waveform).

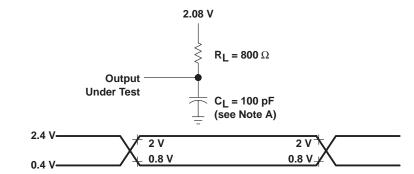
timing requirements for programming

			MIN	NOM	MAX	UNIT
^t w(PGM)	Pulse duration, program	SNAP! Pulse programming algorithm	95	100	105	μs
t _{su(A)}	Setup time, address		2			μs
t _{su(E)}	Setup time, E		2			μs
t _{su(G)}	Setup time, G		2			μs
t _{su(D)}	Setup time, data		2			μs
t _{su(VPP)}	Setup time, V _{PP}		2			μs
t _{su(VCC)}	Setup time, V _{CC}		2			μs
t _{h(A)}	Hold time, address		0			μs
^t h(D)	Hold time, data		2			μs



TMS27C010A 131 072 BY 8-BIT UV ERASABLE TMS27PC010A 131 072 BY 8-BIT PROGRAMMABLE READ-ONLY MEMORIES SMLS110C – NOVEMBER 1990 – REVISED SEPTEMBER 1997

PARAMETER MEASUREMENT INFORMATION



NOTES: A. CL includes probe and fixture capacitance.

B. The ac testing inputs are driven at 2.4 V for logic high and 0.4 V for logic low. Timing measurements are made at 2 V for logic high and 0.8 V for logic low for both inputs and outputs.

Figure 2. The ac Test Output Load Circuit and Waveform

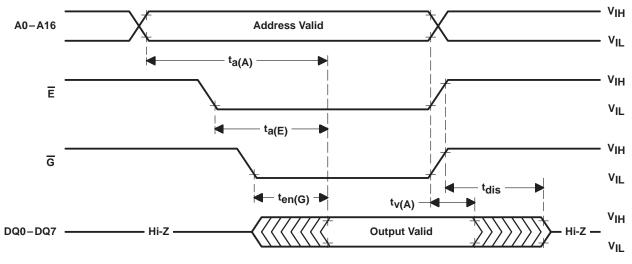
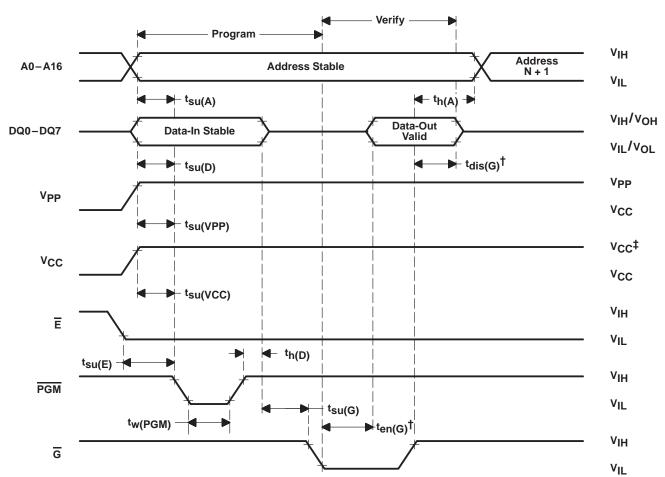


Figure 3. Read-Cycle Timing



SMLS110C - NOVEMBER 1990 - REVISED SEPTEMBER 1997



PROGRAMMING INFORMATION

 † t_{dis(G)} and t_{en(G)} are characteristics of the device but must be accommodated by the programmer. ‡ 13-V V_{PP} and 6.5-V V_{CC} for SNAP! Pulse programming.

Figure 4. Program-Cycle Timing (SNAP! Pulse Programming)



SMLS110C - NOVEMBER 1990 - REVISED SEPTEMBER 1997

PLASTIC J-LEADED CHIP CARRIER

Seating Plane 0.004 (0,10) \bigtriangleup 0.140 (3,56) 0.132 (3,35) 0.495 (12,57) 0.129 (3,28) 0.485 (12,32) 0.123 (3,12) 0.453 (11,51) 0.049 (1,24) 0.447 (11,35) 0.043 (1,09) 0.008 (0,20) NOM 30 4 1 \bigcirc 29 5 0.020 (0,51) 0.015 (0,38) 0.595 (15,11) **Y** 0.585 (14,86) 0.553 (14,05) 0.547 (13,89) 0.030 (0,76) TYP ★ 13 21 14 20 0.050 (1,27) 4040201-4/B 03/95

NOTES: A. All linear dimensions are in inches (millimeters). B. This drawing is subject to change without notice.

C. Falls within JEDEC MS-016

FM (R-PQCC-J32)

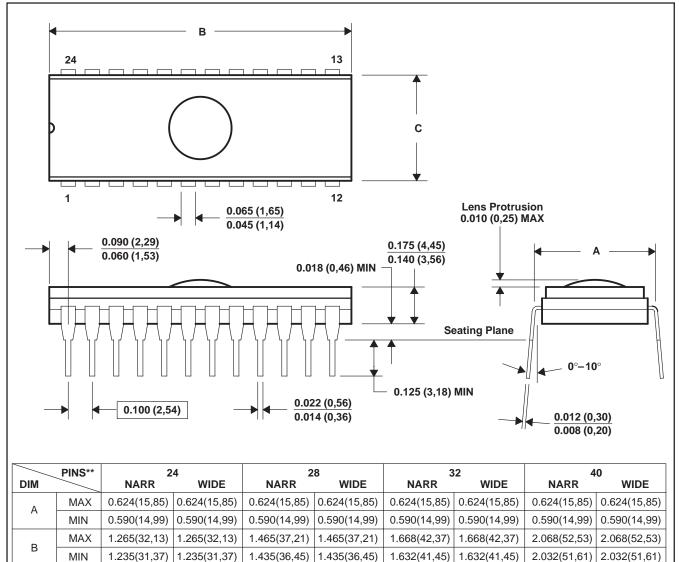


SMLS110C - NOVEMBER 1990 - REVISED SEPTEMBER 1997

J (R-CDIP-T**)

CERAMIC SIDE-BRAZE DUAL-IN-LINE PACKAGE

24 PIN SHOWN



4040084/B 04/95

0.541(13,74)

0.514(13,06)

0.598(15,19)

0.571(14,50)

NOTES: A. All linear dimensions are in inches (millimeters).

0.541(13,74)

0.514(13,06)

MAX

MIN

С

B. This drawing is subject to change without notice.

0.598(15,19)

0.571(14,50)

- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.

0.541(13,74)

0.514(13,06)



0.598(15,19)

0.571(14,50)

0.541(13,74)

0.514(13,06)

0.598(15,19)

0.571(14,50)

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1998, Texas Instruments Incorporated